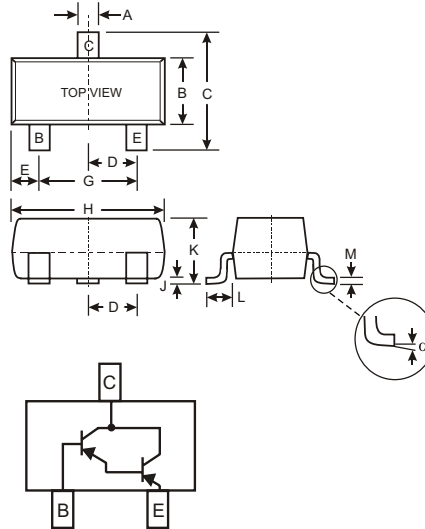


Features

- Epitaxial Planar Die Construction
- Complementary NPN Types Available (MMBTA13 / MMBTA14)
- Ideal for Medium Power Amplification and Switching
- High Current Gain
- Also Available in Lead Free Version

Mechanical Data

- Case: SOT-23, Molded Plastic
- Case material - UL Flammability Rating Classification 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish). Please see Ordering Information, Note 4, on Page 2
- Terminal Connections: See Diagram
- MMBTA63 Marking (See Page 2): K2E, K3E
- MMBTA64 Marking (See Page 2): K3E
- Ordering & Date Code Information: See Page 2
- Weight: 0.008 grams (approx.)



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	MMBTA63	MMBTA64	Unit
Collector-Base Voltage	V_{CBO}	-30		V
Collector-Emitter Voltage	V_{CEO}	-30		V
Emitter-Base Voltage	V_{EBO}	-10		V
Collector Current - Continuous (Note 1)	I_C	-500		mA
Power Dissipation (Note 1)	P_d	300		mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	417		$^\circ\text{C}/\text{W}$
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150		$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)					
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-30	—	V	$I_C = -100\mu\text{A}, V_{BE} = 0\text{V}$
Collector Cutoff Current	I_{CBO}	—	-100	nA	$V_{CB} = -30\text{V}, I_E = 0$
Emitter Cutoff Current	I_{EBO}	—	-100	nA	$V_{EB} = -10\text{V}, I_C = 0$
ON CHARACTERISTICS (Note 2)					
DC Current Gain	MMBTA63 MMBTA64 MMBTA63 MMBTA64	h_{FE}	5,000 10,000 10,000 20,000	—	$I_C = -10\text{mA}, V_{CE} = -5.0\text{V}$ $I_C = -10\text{mA}, V_{CE} = -5.0\text{V}$ $I_C = -100\text{mA}, V_{CE} = -5.0\text{V}$ $I_C = -100\text{mA}, V_{CE} = -5.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-1.5	V	$I_C = -100\text{mA}, I_B = -100\mu\text{A}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	-2.0	V	$I_C = -100\text{mA}, V_{CE} = -5.0\text{V}$
SMALL SIGNAL CHARACTERISTICS					
Current Gain-Bandwidth Product	f_T	125	—	MHz	$V_{CE} = -5.0\text{V}, I_C = -10\text{mA}, f = 100\text{MHz}$

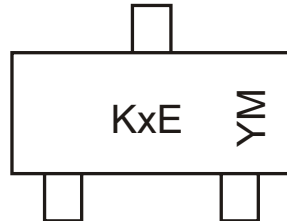
- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. Short duration test pulse used to minimize self-heating effect.

Ordering Information (Note 3)

Device	Packaging	Shipping
MMBTA63-7 MMBTA64-7	SOT-23	3000/Tape & Reel

- Notes: 3. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.
 4. For Lead Free version (with Lead Free terminal finish) part number, please add "-F" suffix to part number above.
 Example: MMBTA64-7-F.

Marking Information

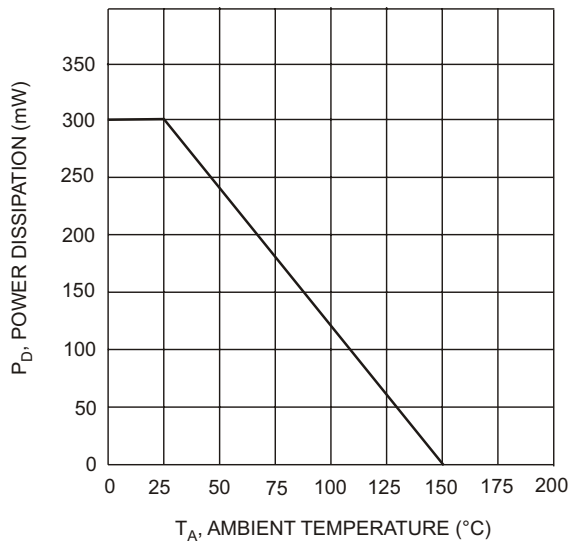


KxE = Product Type Marking Code, ex: K2E = MMBTA63
 YM = Date Code Marking
 Y = Year ex: N = 2002

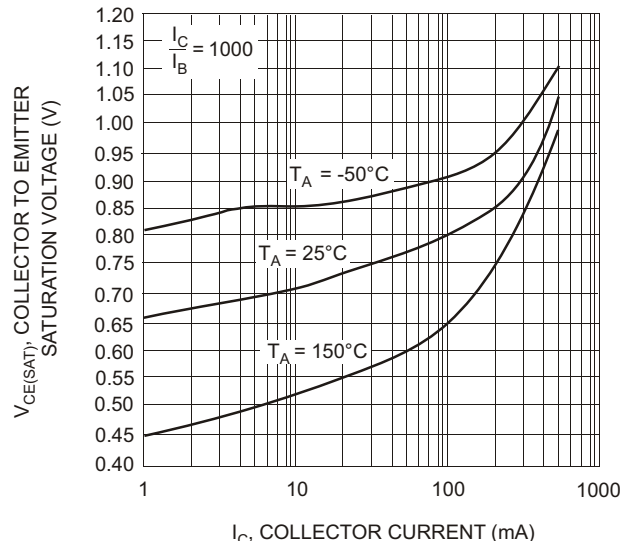
Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



T_A, AMBIENT TEMPERATURE (°C)
 Fig. 1, Max Power Dissipation vs Ambient Temperature



I_C, COLLECTOR CURRENT (mA)
 Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

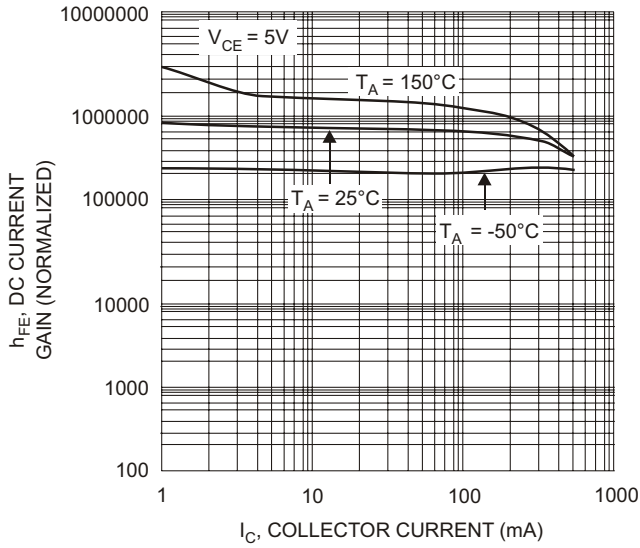


Fig. 3, DC Current Gain vs Collector Current

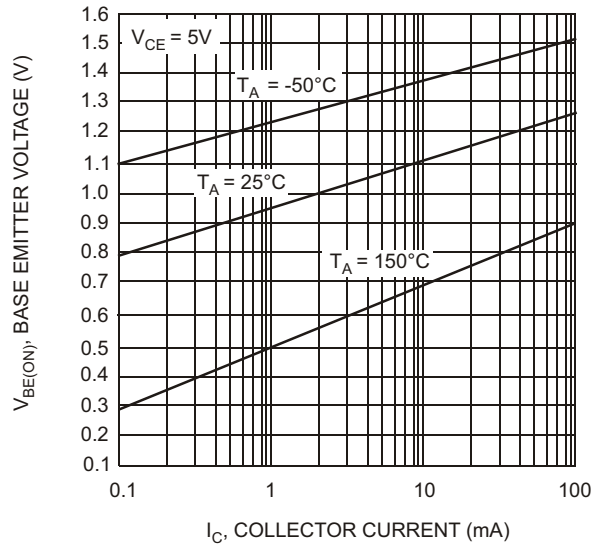


Fig. 4, Base Emitter Voltage vs. Collector Current

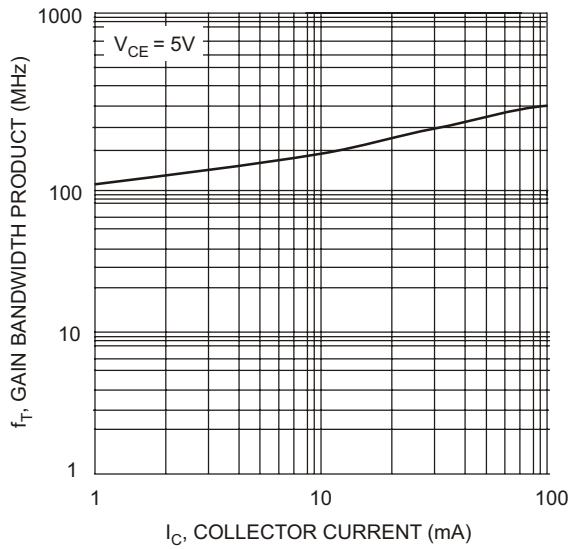


Fig. 5, Gain Bandwidth Product vs. Collector Current